

IN THE CLAIMS

Claims 1 - 16 (Canceled).

17. (Previously Presented) An integrated circuit (IC) comprising:
a substrate comprising at least one level of interconnection;
an insulating layer formed directly on a surface of the substrate;
at least one bond pad formed directly on the insulating layer, the at least one
bond pad coupled through the insulating layer to the at least one level of
interconnection of the substrate;
an adhesion layer formed on a surface of the insulating layer such that the
insulating layer is disposed between the adhesion layer and the substrate; and
a passivation layer formed on a surface of said adhesion layer and a portion of a
surface of the bond pad that is less than the entire surface.

18. (Previously Presented) The integrated circuit of claim 17, wherein the
passivation layer is a first passivation layer, the integrated circuit further comprising a
second passivation layer formed upon said first passivation layer.

19. (Previously Presented) The integrated circuit of claim 17, wherein said
insulating layer comprises an oxide layer comprising silicon dioxide (SiO₂).

20. (Previously Presented) The integrated circuit of claim 17, wherein said
adhesion layer includes silicon oxynitride.

21. (Previously Presented) The integrated circuit of claim 17, wherein said
passivation layer includes silicon nitride (Si₃N₄).

22. (Previously Presented) The integrated circuit of claim 18, wherein said
second passivation layer includes polyimide.

23. (Withdrawn) An integrated circuit comprising in a four layer stack:
a silicon dioxide insulating layer;

a silicon oxynitride adhesion layer formed on a surface of said silicon dioxide insulating layer by treating said surface of said silicon dioxide insulating layer with a gas;

a silicon nitride hard passivation layer formed directly on a surface of said silicon oxynitride adhesion layer; and

a photodefinaible polyimide soft passivation layer formed on said silicon nitride hard passivation layer.

24. (Canceled).

25. (Withdrawn) The integrated circuit of claim 17, wherein said gas includes one of oxygen and nitrogen (N), oxygen and ammonia (NH₃), oxygen and argon (Ar) and ozone (O₃) and argon.

26. (Withdrawn) The integrated circuit of claim 23, wherein said gas includes one of oxygen and nitrogen (N), oxygen and ammonia (NH₃), oxygen and argon (Ar) and ozone (O₃) and argon.

27. (Previously Presented) An integrated circuit comprising:

a substrate;

an insulating layer formed on the substrate;

at least one bond pad formed directly on the insulating layer;

a composite film comprising:

a first layer, and

a second layer of a material different than a material of the first layer, wherein the first layer is disposed between the insulating layer and the second layer,

wherein the first layer and the second layer comprise one common chemical element other than silicon, and

wherein the second layer is a passivation layer formed on the first layer and a portion of a surface of the bond pad that is less than the entire surface.

28. (Previously Presented) The integrated circuit of claim 27, wherein said first layer includes silicon oxynitride.

29. (Previously Presented) The integrated circuit of claim 28, wherein said second layer includes silicon nitride (Si_3N_4).